

Модуль тиристорно-диодный АМКН 26



V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 50$ A (maximum value for continuous operation) $I_{TAV} = 32$ A (sin 180; $T_c = 68$ °C)	
500	400	—	AMKH 26-04D
700	600	AMKT 26-06D	AMKH 26-06D
900	800	AMKT 26-08D	AMKH 26-08D
1300	1200	AMKT 26-12E	AMKH 26-12E
1500	1400	AMKT 26-14E	AMKH 26-14E
1700	1600	AMKT 26-16E	AMKH 26-16E

Symbol	Conditions	AMKT 26 AMKH 26	Units
I_{TAV}	sin. 180; $T_{case} = 68$ °C	32	A
	$T_{case} = 85$ °C	25	A
I_D	B2/B6 $T_{amb} = 45$ °C; P 3/180	38	A
	$T_{amb} = 35$ °C; P 3/180 F	60	A
I_{RMS}	W1/W3 $T_{amb} = 45$ °C; P 3/180	52 / 3 x 37	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms	550	A
	$T_{vj} = 125$ °C; 10 ms	480	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	1 500	A ² s
	$T_{vj} = 125$ °C; 8,3 ... 10 ms	1 150	A ² s
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 \cdot V_{DRM}$	1	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	150	A/μs
t_q	$T_{vj} = 125$ °C	typ. 80	μs
I_H	$T_{vj} = 25$ °C; typ./max.	100	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ ° ; typ./max.	250	mA
V_T	$T_{vj} = 25$ °C; $I_T = 75$ A	max. 1,8	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	0,9	V
r_T	$T_{vj} = 125$ °C	12	m°
$I_{DD}; I_{RD}$	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}$ $V_{DD} = V_{DRM}$	max. 10	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	5	mA
R_{thjc}	cont. } per thyristor / sin. 180 } per module rec. 120 }	0,9 0,95 1,0	°C/W °C/W °C/W
R_{thch}		0,2	°C/W
T_{vj}		-40 ... + 125	°C
T_{stg}		-40 ... + 125	°C
V_{isol}	a.c. 50 Hz; r.m.s; 1 s/1 min	3600	V~
M_1	to heatsink } SI (US) units to terminals }	5 (44 lb. in.) ± 15 % ²⁾	Nm
M_2		3 (26 lb. in.) ± 15 %	Nm
a		5 · 9,81	m/s ²
w	approx.	95	g

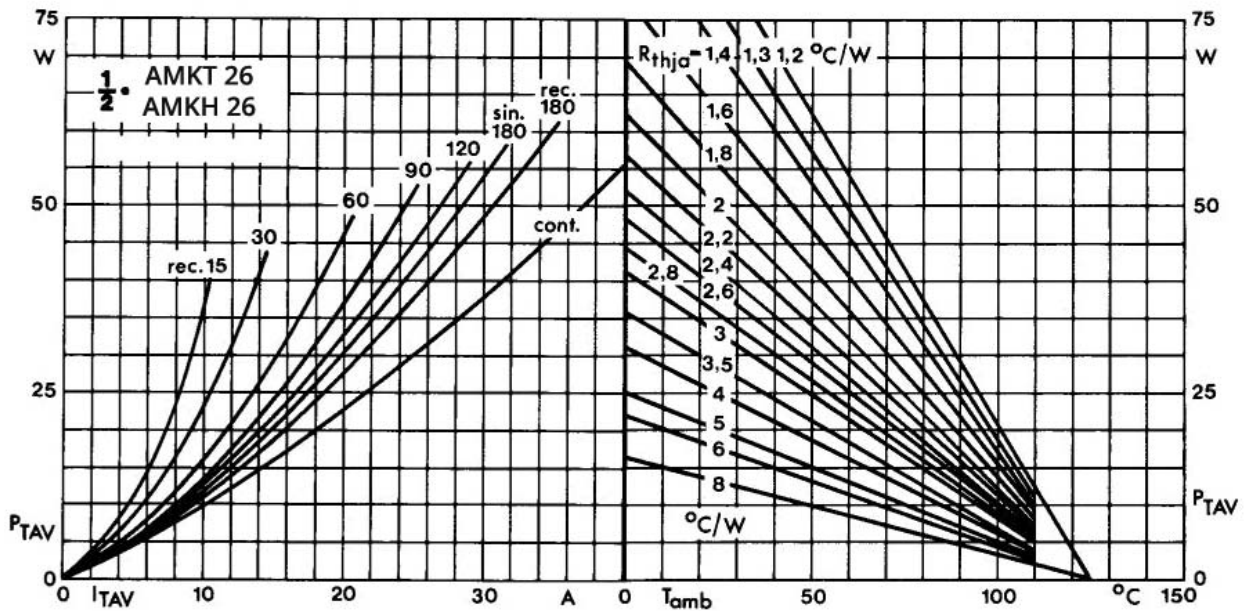


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

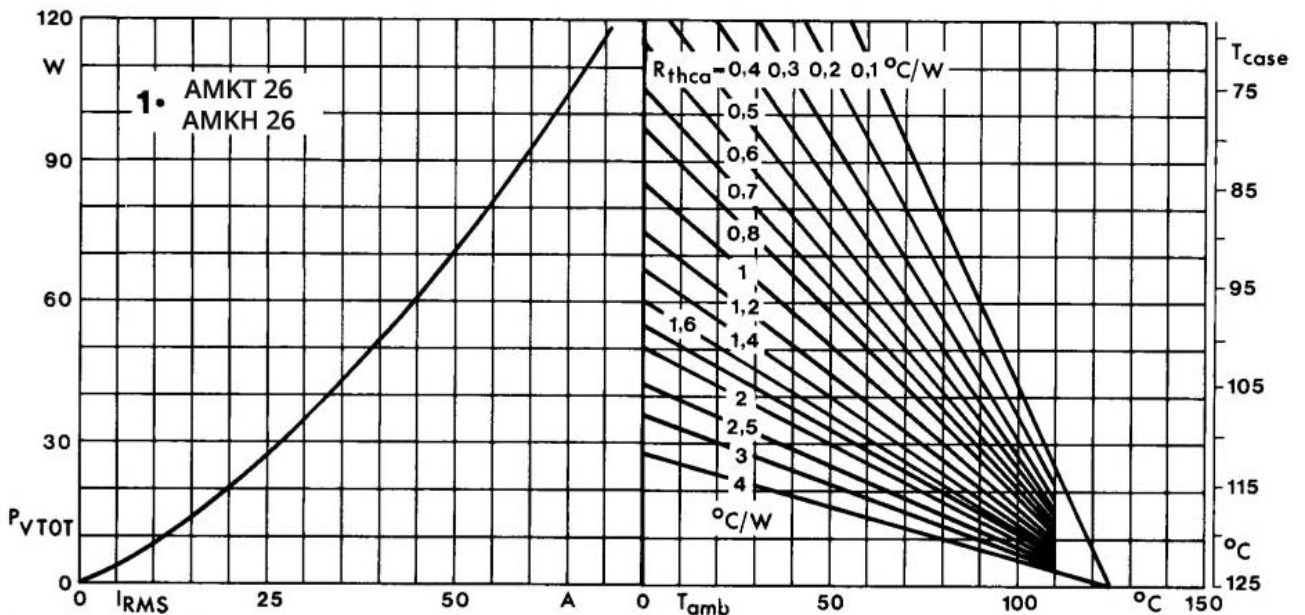


Fig. 2 Power dissipation per module vs. rms current and case temperature

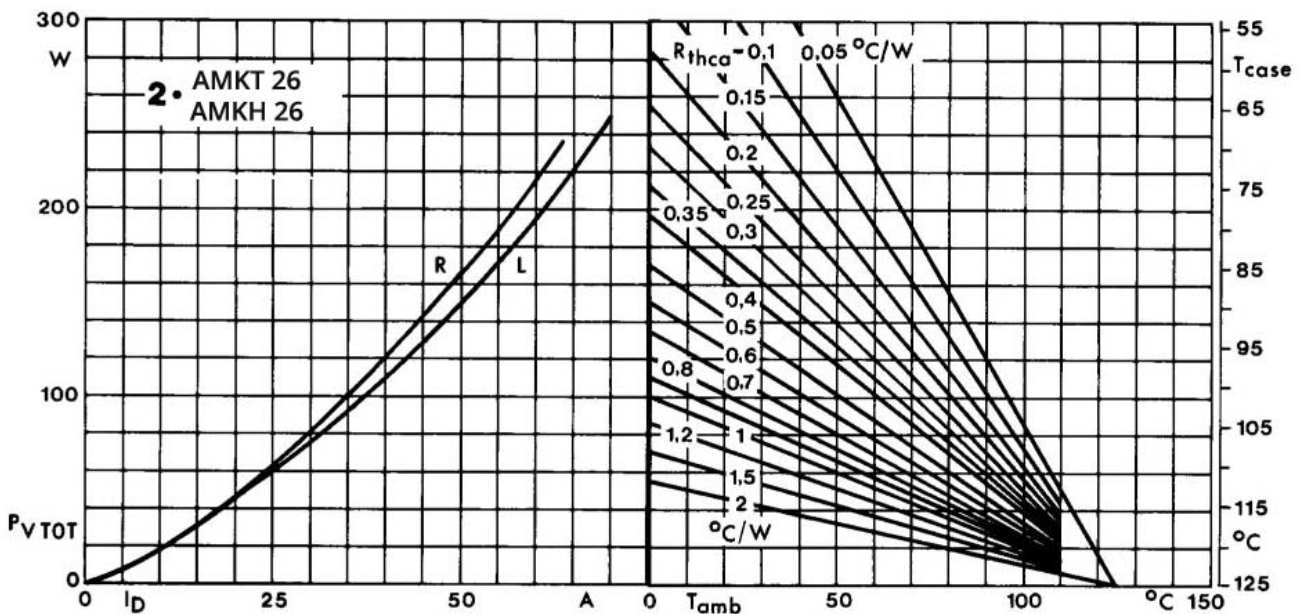


Fig. 3 Power dissipation of two modules vs. direct current and case temperature

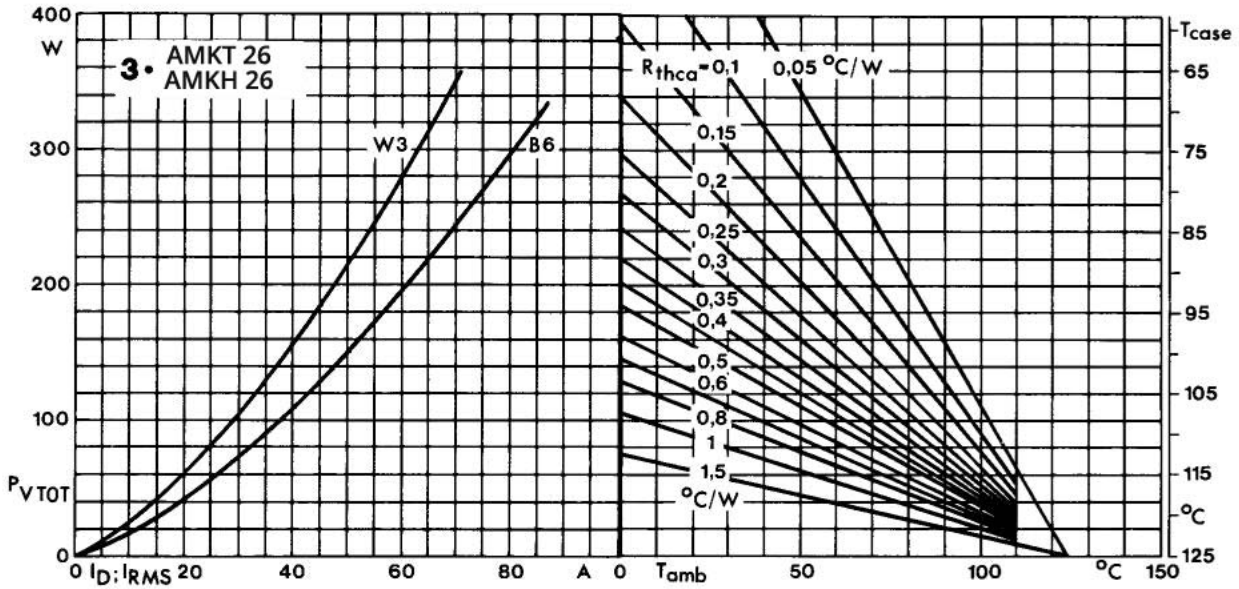


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

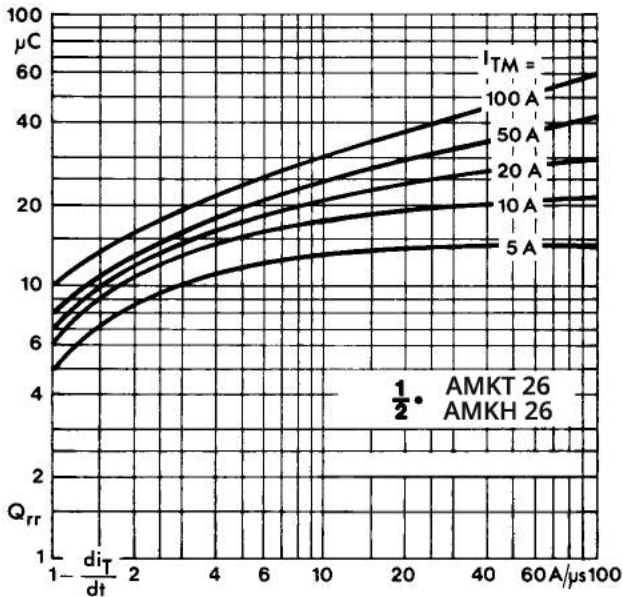


Fig. 5 Recovered charge vs. current decrease

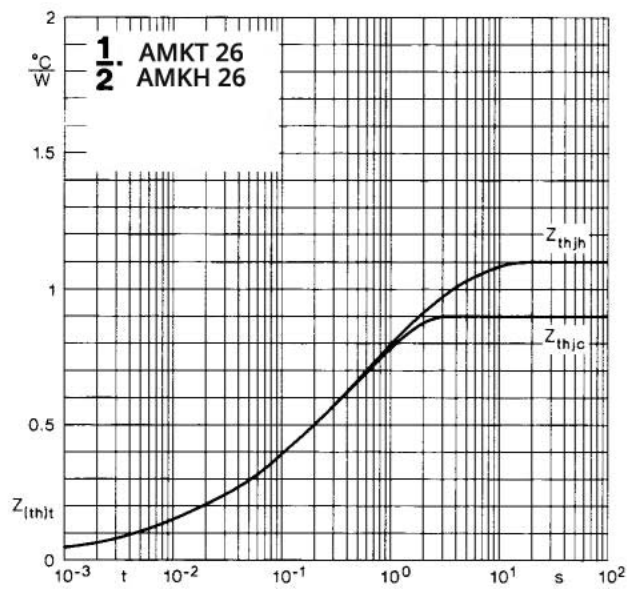


Fig. 6 Transient thermal impedance vs. time

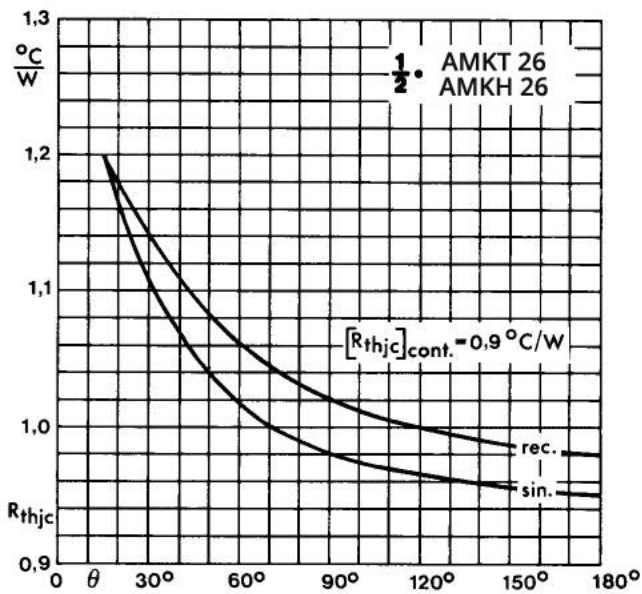


Fig. 7 Thermal resistance vs. conduction angle

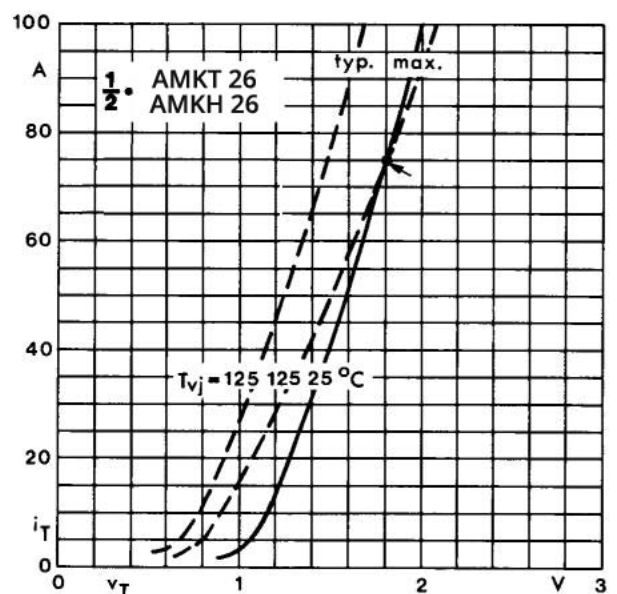


Fig. 8 On-state characteristics

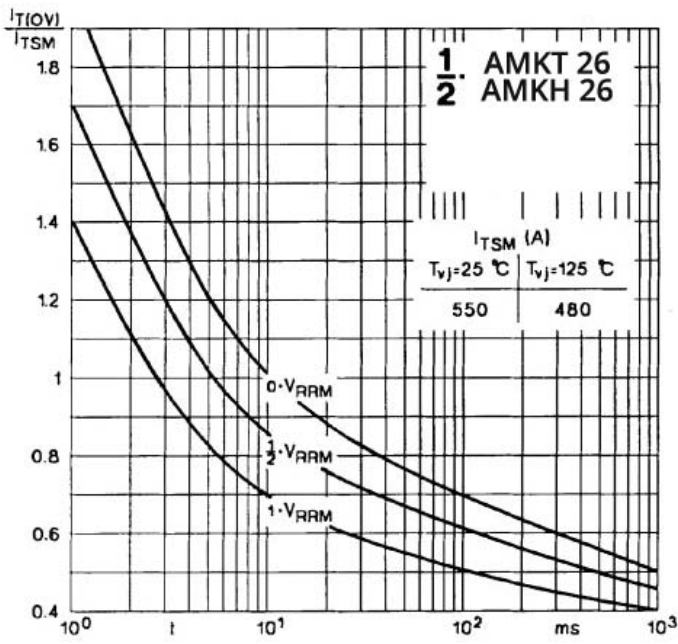


Fig. 9 Surge overload current vs. time

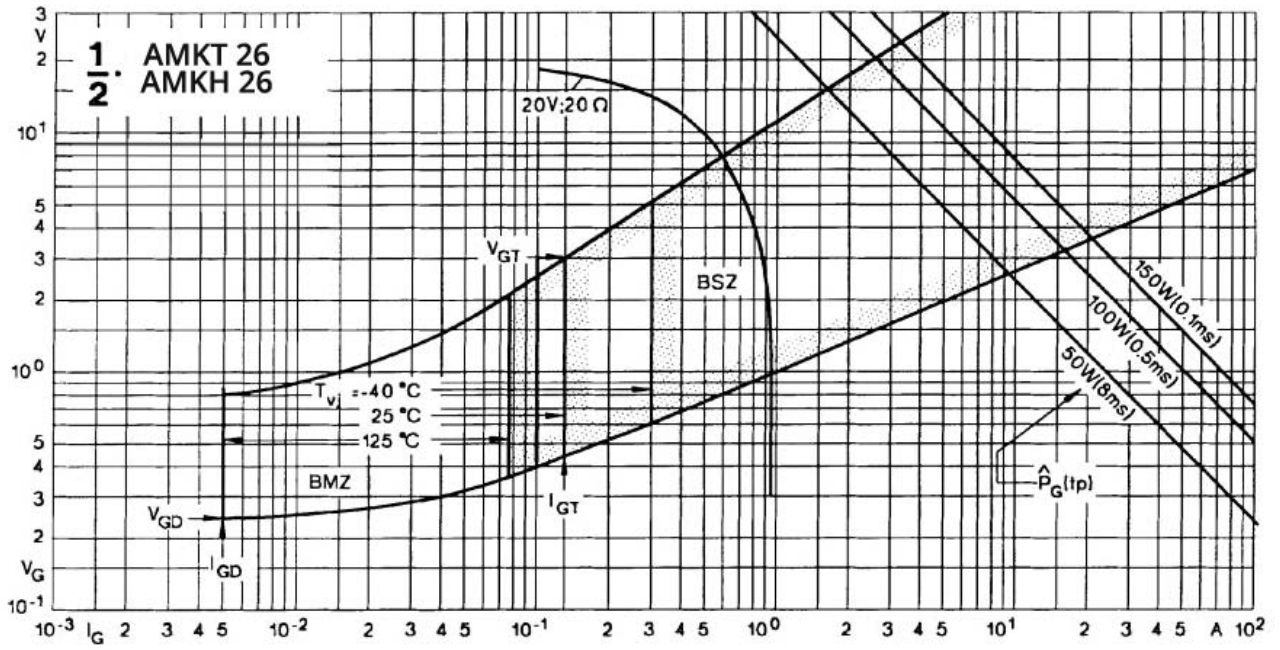
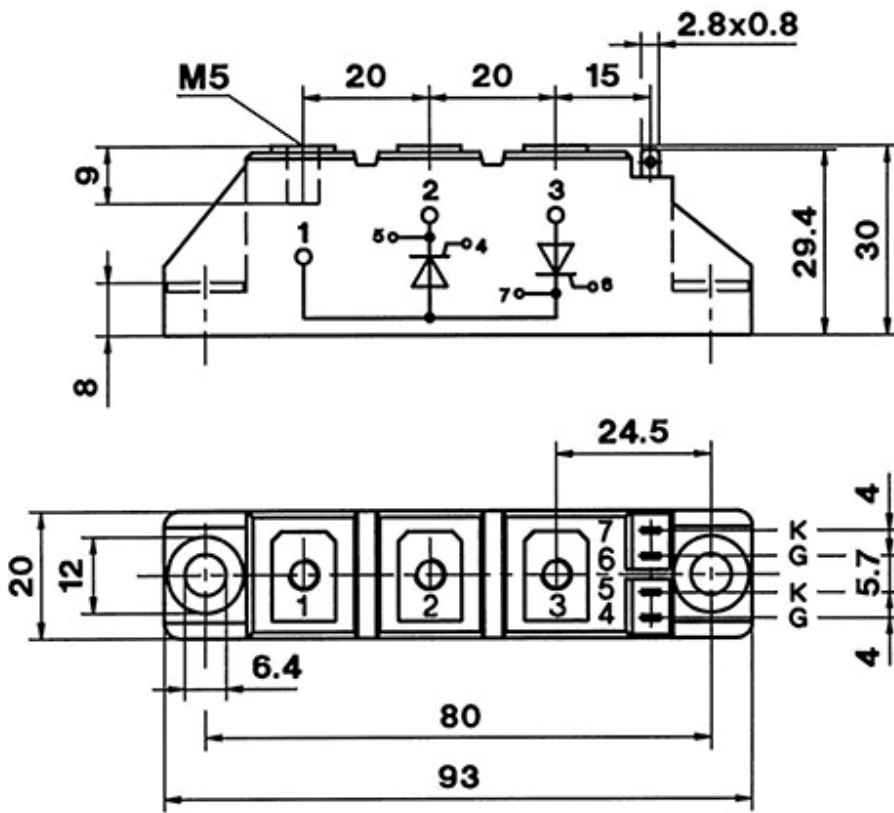


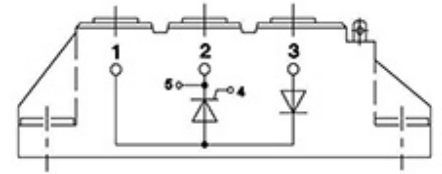
Fig. 10 Gate trigger characteristics

DIMENSIONS

AMKT



AMKH



Dimensions in mm

TOPOLOGY OF INTERNAL CONNECTION

